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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	64
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 17x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LFQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101mjdfb-50

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1-1. List of Ordering Part Numbers

(2/12)

				(2/12)
Pin	Package	Data	Fields of	Ordering Part Number
count		flash	Application	
			Note	
25 pins	25-pin plastic	Mounted	Α	R5F1008AALA#U0, R5F1008CALA#U0, R5F1008DALA#U0,
25 pins	· · ·	Mounted	7.	R5F1008EALA#U0
	WFLGA (3 \times 3 mm,			R5F1008AALA#W0, R5F1008CALA#W0, R5F1008DALA#W0,
	0.5 mm pitch)			R5F1008EALA#W0
			G	R5F1008AGLA#U0, R5F1008CGLA#U0, R5F1008DGLA#U0,
				R5F1008EGLA#U0
				R5F1008AGLA#W0, R5F1008CGLA#W0, R5F1008DGLA#W0,
				R5F1008EGLA#W0
		Not	Α	R5F1018AALA#U0, R5F1018CALA#U0, R5F1018DALA#U0,
i		mounted		R5F1018EALA#U0
				R5F1018AALA#W0, R5F1018CALA#W0, R5F1018DALA#W0,
				R5F1018EALA#W0
30 pins	30-pin plastic LSSOP	Mounted	Α	R5F100AAASP#V0, R5F100ACASP#V0, R5F100ADASP#V0,
i	(7.62 mm (300), 0.65			R5F100AEASP#V0, R5F100AFASP#V0, R5F100AGASP#V0
	mm pitch)			R5F100AAASP#X0, R5F100ACASP#X0, R5F100ADASP#X0
	min piton)		_	R5F100AEASP#X0, R5F100AFASP#X0, R5F100AGASP#X0
			D	R5F100AADSP#V0, R5F100ACDSP#V0, R5F100ADDSP#V0,
				R5F100AEDSP#V0, R5F100AFDSP#V0, R5F100AGDSP#V0
				R5F100AADSP#X0, R5F100ACDSP#X0, R5F100ADDSP#X0, R5F100AEDSP#X0, R5F100AFDSP#X0, R5F100AGDSP#X0
			G	R5F100AGSP#V0, R5F100ACGSP#V0,
			G	R5F100ADGSP#V0, R5F100ACGSF#V0,
				R5F100AFGSP#V0, R5F100AGGSP#V0,
				R5F100AAGSP#X0, R5F100ACGSP#X0,
				R5F100ADGSP#X0,R5F100AEGSP#X0,
				R5F100AFGSP#X0, R5F100AGGSP#X0
		Not	Α	R5F101AAASP#V0, R5F101ACASP#V0, R5F101ADASP#V0,
				R5F101AEASP#V0, R5F101AFASP#V0, R5F101AGASP#V0
		mounted		R5F101AAASP#X0, R5F101ACASP#X0, R5F101ADASP#X0,
				R5F101AEASP#X0, R5F101AFASP#X0, R5F101AGASP#X0
			D	R5F101AADSP#V0, R5F101ACDSP#V0, R5F101ADDSP#V0,
				R5F101AEDSP#V0, R5F101AFDSP#V0, R5F101AGDSP#V0
				R5F101AADSP#X0, R5F101ACDSP#X0, R5F101ADDSP#X0,
				R5F101AEDSP#X0, R5F101AFDSP#X0, R5F101AGDSP#X0
32 pins	32-pin plastic	Mounted	Α	R5F100BAANA#U0, R5F100BCANA#U0, R5F100BDANA#U0,
	HWQFN (5 × 5 mm,			R5F100BEANA#U0, R5F100BFANA#U0, R5F100BGANA#U0
	0.5 mm pitch)			R5F100BAANA#W0, R5F100BCANA#W0, R5F100BDANA#W0,
	0.5 min pitch)			R5F100BEANA#W0, R5F100BFANA#W0, R5F100BGANA#W0
			D	R5F100BADNA#U0, R5F100BCDNA#U0, R5F100BDDNA#U0,
				R5F100BEDNA#U0, R5F100BFDNA#U0, R5F100BGDNA#U0
				R5F100BADNA#W0, R5F100BCDNA#W0, R5F100BDDNA#W0,
				R5F100BEDNA#W0, R5F100BFDNA#W0, R5F100BGDNA#W0
			G	R5F100BAGNA#U0, R5F100BCGNA#U0, R5F100BDGNA#U0,
				R5F100BEGNA#U0, R5F100BFGNA#U0, R5F100BGGNA#U0
				R5F100BAGNA#W0, R5F100BCGNA#W0, R5F100BDGNA#W0,
			_	R5F100BEGNA#W0, R5F100BFGNA#W0, R5F100BGGNA#W0
		Not	Α	R5F101BAANA#U0, R5F101BCANA#U0, R5F101BDANA#U0,
		mounted		R5F101BEANA#U0, R5F101BFANA#U0, R5F101BGANA#U0
				R5F101BAANA#W0, R5F101BCANA#W0, R5F101BDANA#W0,
			D	R5F101BEANA#W0, R5F101BFANA#W0, R5F101BGANA#W0
			٦ ا	R5F101BADNA#U0, R5F101BCDNA#U0, R5F101BDDNA#U0, R5F101BEDNA#U0, R5F101BEDNA#U0
1				R5F101BADNA#W0, R5F101BCDNA#W0, R5F101BDDNA#W0,
				R5F101BEDNA#W0, R5F101BCDNA#W0, R5F101BBDNA#W0,
			1	TOT TO TO EDINA#WO, NOT TO TO FOUNA#WO, NOT TO TO EDINA#WO

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



Table 1-1. List of Ordering Part Numbers

(5/12)

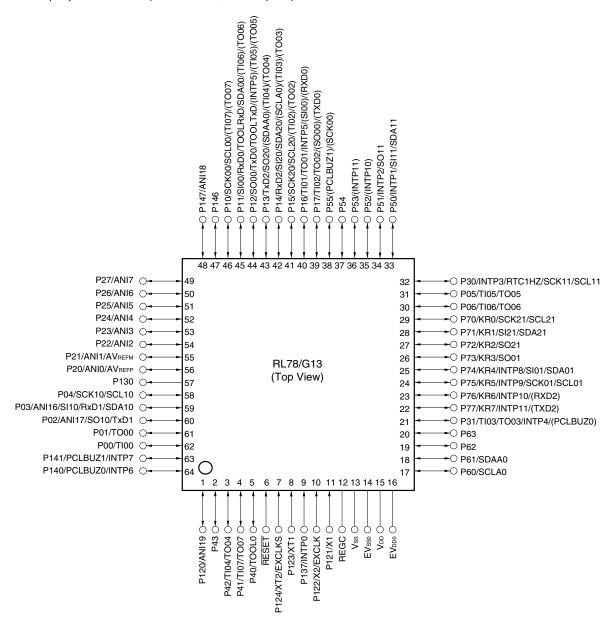
Pin	Package	Data	Fields of	Ordering Part Number
count		flash	Application	
			Note	
48 pins	48-pin plastic	Mounted	Α	R5F100GAAFB#V0, R5F100GCAFB#V0, R5F100GDAFB#V0,
	LFQFP (7×7 mm,			R5F100GEAFB#V0, R5F100GFAFB#V0, R5F100GGAFB#V0,
	0.5 mm pitch)			R5F100GHAFB#V0, R5F100GJAFB#V0, R5F100GKAFB#V0,
				R5F100GLAFB#V0
				R5F100GAAFB#X0, R5F100GCAFB#X0, R5F100GDAFB#X0,
				R5F100GEAFB#X0, R5F100GFAFB#X0, R5F100GGAFB#X0,
				R5F100GHAFB#X0, R5F100GJAFB#X0, R5F100GKAFB#X0,
				R5F100GLAFB#X0
			D	R5F100GADFB#V0, R5F100GCDFB#V0, R5F100GDDFB#V0,
				R5F100GEDFB#V0, R5F100GFDFB#V0, R5F100GGDFB#V0,
				R5F100GHDFB#V0, R5F100GJDFB#V0, R5F100GKDFB#V0,
				R5F100GLDFB#V0
				R5F100GADFB#X0, R5F100GCDFB#X0, R5F100GDDFB#X0,
				R5F100GEDFB#X0, R5F100GFDFB#X0, R5F100GGDFB#X0,
				R5F100GHDFB#X0, R5F100GJDFB#X0, R5F100GKDFB#X0,
				R5F100GLDFB#X0
			G	R5F100GAGFB#V0, R5F100GCGFB#V0, R5F100GDGFB#V0,
				R5F100GEGFB#V0, R5F100GFGFB#V0, R5F100GGGFB#V0,
				R5F100GHGFB#V0, R5F100GJGFB#V0
				R5F100GAGFB#X0, R5F100GCGFB#X0, R5F100GDGFB#X0,
				R5F100GEGFB#X0, R5F100GFGFB#X0, R5F100GGGFB#X0,
				R5F100GHGFB#X0, R5F100GJGFB#X0
		Not	Α	R5F101GAAFB#V0, R5F101GCAFB#V0, R5F101GDAFB#V0,
		mounted		R5F101GEAFB#V0, R5F101GFAFB#V0, R5F101GGAFB#V0,
				R5F101GHAFB#V0, R5F101GJAFB#V0, R5F101GKAFB#V0,
				R5F101GLAFB#V0
				R5F101GAAFB#X0, R5F101GCAFB#X0, R5F101GDAFB#X0,
				R5F101GEAFB#X0, R5F101GFAFB#X0, R5F101GGAFB#X0,
				R5F101GHAFB#X0, R5F101GJAFB#X0, R5F101GKAFB#X0,
				R5F101GLAFB#X0
			D	R5F101GADFB#V0, R5F101GCDFB#V0, R5F101GDDFB#V0,
				R5F101GEDFB#V0, R5F101GFDFB#V0, R5F101GGDFB#V0,
				R5F101GHDFB#V0, R5F101GJDFB#V0, R5F101GKDFB#V0,
				R5F101GLDFB#V0
				R5F101GADFB#X0, R5F101GCDFB#X0, R5F101GDDFB#X0,
				R5F101GEDFB#X0, R5F101GFDFB#X0, R5F101GGDFB#X0,
1				R5F101GHDFB#X0, R5F101GJDFB#X0, R5F101GKDFB#X0,
				R5F101GLDFB#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.11 64-pin products

- 64-pin plastic LQFP (12 x 12 mm, 0.65 mm pitch)
- 64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)

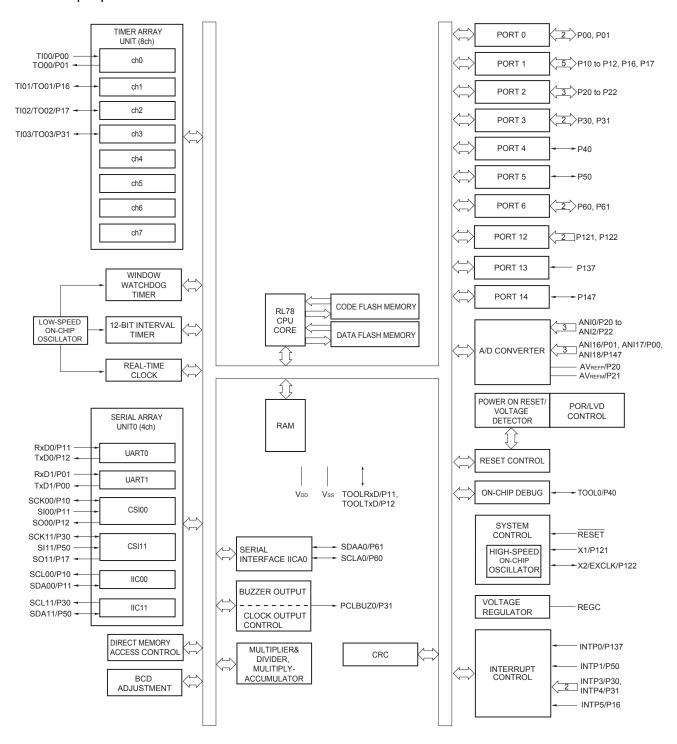


- Cautions 1. Make EVsso pin the same potential as Vss pin.
 - 2. Make VDD pin the potential that is higher than EVDDO pin.
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the Vss and EV_{SS0} pins to separate ground lines.
- **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register** (**PIOR**) in the RL78/G13 User's Manual.

1.5.2 24-pin products



 The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/G13 User's Manual).

(2/2)

						(2/2)				
Ite	m	80-	pin	100	-pin	128	3-pin			
		R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx			
Clock output/buzz	er output		2	1	2		2			
		• 2.44 kHz, 4.8	8 kHz, 9.76 kHz,	1.25 MHz, 2.5 M	Hz, 5 MHz, 10 M	ИHz				
		· ·	clock: fmain = 20							
			• 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: fsub = 32.768 kHz operation)							
0/40 1 "	A /D		CIOCK: ISUB = 32.70			I				
8/10-bit resolution	A/D converter	17 channels		20 channels		26 channels				
Serial interface			, 128-pin product							
			•	2 channels/UAR						
				2 channels/UAR		tina I IN-hus): 1 (channel			
		 CSI: 2 channels/simplified l²C: 2 channels/UART (UART supporting LIN-bus): 1 channel CSI: 2 channels/simplified l²C: 2 channels/UART: 1 channel 								
	I ² C bus	2 channels	·	2 channels		2 channels				
Multiplier and divid	der/multiply-	• 16 bits × 16 bi	ts = 32 bits (Uns	igned or signed)						
accumulator		• 32 bits ÷ 32 bi	ts = 32 bits (Uns	igned)						
		• 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)								
DMA controller		4 channels								
Vectored	Internal		37 37			41				
interrupt sources	External		13	1	3		13			
Key interrupt			8	1	8		8			
Reset		Reset by RES								
			by watchdog tim							
			by power-on-res by voltage detec							
				tion execution Note						
			by RAM parity e							
			by illegal-memor							
Power-on-reset cir	rcuit	Power-on-res	et: 1.51 V (TY	P.)						
		Power-down-	reset: 1.50 V (TY	P.)						
Voltage detector		Rising edge :		.06 V (14 stages))					
		Falling edge: 1.63 V to 3.98 V (14 stages)								
On-chip debug fur	nction	Provided								
Power supply volta	age	$V_{DD} = 1.6 \text{ to } 5.5$	$V (T_A = -40 \text{ to } +8$	5°C)						
		$V_{DD} = 2.4 \text{ to } 5.5 \text{ V } (T_A = -40 \text{ to } +105^{\circ}\text{C})$								
Operating ambien	t temperature	$T_A = 40 \text{ to } +85^\circ$	C (A: Consumer	applications, D: Ir	ndustrial applicat	ions)				
		$T_A = 40 \text{ to } +105$	°C (G: Industrial	applications)						
		1								



Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.



2. ELECTRICAL SPECIFICATIONS (TA = -40 to +85°C)

This chapter describes the following electrical specifications.

Target products A: Consumer applications $T_A = -40$ to $+85^{\circ}C$

R5F100xxAxx, R5F101xxAxx

D: Industrial applications T_A = −40 to +85°C

R5F100xxDxx, R5F101xxDxx

G: Industrial applications when $T_A = -40$ to $+105^{\circ}C$ products is used in the range of $T_A = -40$ to $+85^{\circ}C$

R5F100xxGxx

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. With products not provided with an EV_{DD0}, EV_{DD1}, EV_{SS0}, or EV_{SS1} pin, replace EV_{DD0} and EV_{DD1} with V_{DD}, or replace EV_{SS0} and EV_{SS1} with V_{SS}.
 - 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.



2.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25$ °C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
	EV _{DD0} , EV _{DD1}	EV _{DD0} = EV _{DD1}	-0.5 to +6.5	V
	EVsso, EVss1	EVsso = EVss1	-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	Vıı	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147		V
	V _{I2}	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	Vo ₁	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147		٧
	V _{O2}	P20 to P27, P150 to P156	-0.3 to V _{DD} +0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI26	-0.3 to EV _{DD0} +0.3 and -0.3 to AV _{REF} (+) +0.3 ^{Notes 2,3}	V
	V _{Al2}	ANI0 to ANI14	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF} (+) +0.3 Notes 2, 3	V

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** $AV_{REF}(+)$: + side reference voltage of the A/D converter.
 - 3. Vss: Reference voltage

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (2/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	lo _{L1}	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147				20.0 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P07, P32 to	$4.0~V \leq EV_{DD0} \leq 5.5~V$			70.0	mA
		P37, P40 to P47, P102 to P106, P120,	$2.7~V \leq EV_{DD0} < 4.0~V$			15.0	mA
		P125 to P127, P130, P140 to P145	$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			9.0	mA
		(,	$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			4.5	mA
			$4.0~V \leq EV_{DD0} \leq 5.5~V$			80.0	mA
		P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97.	$2.7~V \leq EV_{DD0} < 4.0~V$			35.0	mA
		P100, P101, P110 to P117, P146,	$1.8~V \leq EV_{DD0} < 2.7~V$			20.0	mA
		P147 (When duty ≤ 70% Note 3)	$1.6~V \le EV_{DD0} < 1.8~V$			10.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				150.0	mA
	lo _{L2}	Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	$1.6~V \leq V_{DD} \leq 5.5~V$			5.0	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1 and Vss pin.
 - 2. However, do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(lol \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and lol = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V) (1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}	Operating	HS (high-	fin = 32 MHz ^{Note 3}	Basic	$V_{DD} = 5.0 \text{ V}$		2.1		mA
current Note 1		mode	speed main) mode Note 5		operation	$V_{DD} = 3.0 \text{ V}$		2.1		mA
			mode		Normal	$V_{DD} = 5.0 \text{ V}$		4.6	7.0	mA
					operation	V _{DD} = 3.0 V		4.6	7.0	mA
				fin = 24 MHz Note 3	Normal	V _{DD} = 5.0 V		3.7	5.5	mA
					operation	V _{DD} = 3.0 V		3.7	5.5	mA
				fin = 16 MHz Note 3	Normal	V _{DD} = 5.0 V		2.7	4.0	mA
					operation	V _{DD} = 3.0 V		2.7	4.0	mA
			LS (low-	fin = 8 MHz Note 3	Normal	$V_{DD} = 3.0 \text{ V}$		1.2	1.8	mA
			speed main) mode Note 5		operation	V _{DD} = 2.0 V		1.2	1.8	mA
			LV (low-	fin = 4 MHz Note 3	Normal	$V_{DD} = 3.0 \text{ V}$		1.2	1.7	mA
			voltage main) mode		operation	V _{DD} = 2.0 V		1.2	1.7	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.0	4.6	mA
			speed main) mode Note 5	V _{DD} = 5.0 V	operation	Resonator connection		3.2	4.8	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.0	4.6	mA
			V _{DD} = 3.0 V	operation	Resonator connection		3.2	4.8	mA	
			$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		1.9	2.7	mA	
			LS (low-	V _{DD} = 5.0 V	operation	Resonator connection		1.9	2.7	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		1.9	2.7	mA
				V _{DD} = 3.0 V	operation	Resonator connection		1.9	2.7	mA
				fmx = 8 MHz ^{Note 2} , Normal	Square wave input		1.1	1.7	mA	
			speed main) mode Note 5	V _{DD} = 3.0 V	operation	Resonator connection		1.1	1.7	mA
				$f_{MX} = 8 MHz^{Note 2},$	Normal	Square wave input		1.1	1.7	mA
				V _{DD} = 2.0 V	operation	Resonator connection		1.1	1.7	mA
			Subsystem	fsuв = 32.768 kHz	Normal	Square wave input		4.1	4.9	μА
			clock operation	Note 4 $T_A = -40^{\circ}C$	operation	Resonator connection		4.2	5.0	μА
				fsuB = 32.768 kHz	Normal	Square wave input		4.1	4.9	μA
				Note 4 TA = +25°C	operation	Resonator connection		4.2	5.0	μА
				fsuB = 32.768 kHz	Normal	Square wave input		4.2	5.5	μΑ
				Note 4 $T_A = +50^{\circ}C$	operation	Resonator connection		4.3	5.6	μА
				fsuв = 32.768 kHz	Normal	Square wave input		4.3	6.3	μΑ
			Note 4 TA = +70°C	operation	Resonator connection		4.4	6.4	μА	
				fsuB = 32.768 kHz	Normal	Square wave input		4.6	7.7	μА
				Note 4 $T_A = +85^{\circ}C$	operation	Resonator connection		4.7	7.8	μА

(Notes and Remarks are listed on the next page.)



- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVSSO, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V \leq VDD \leq 5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 16 MHz

LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz}$ to 8 MHz LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz}$ to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - **3.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 32 MHz

 $2.4~V \leq V_{DD} \leq 5.5~V @ 1~MHz$ to 16 MHz

LS (low-speed main) mode: $1.8~V \le V_{DD} \le 5.5~V~@1~MHz$ to 8~MHz LV (low-voltage main) mode: $1.6~V \le V_{DD} \le 5.5~V~@1~MHz$ to 4~MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),

g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2)

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Condit	, •	h-speed Mode	,	v-speed Mode	LV (low-voltage main) Mode		Unit	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy2	$4.0~V \leq EV_{DD0} \leq 5.5$	20 MHz < fмск	8/fмск		_		_		ns
Note 5		V	fмcκ ≤ 20 MHz	6/ƒмск		6/fмск		6/fмск		ns
		$2.7~V \le EV_{DD0} \le 5.5$ V	16 MHz < fмск	8/fмск		_		_		ns
			fмск ≤ 16 MHz	6/ƒмск		6/fмск		6/fмск		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		6/fмск and 500		6/fмск and 500		6/fмск and 500		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V	6/fмск and 750		6/fмск and 750		6/fмск and 750		ns	
		$1.7~V \leq EV_{DD0} \leq 5.5~V$		6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5	_		6/fмск and 1500		6/fмск and 1500		ns	
SCKp high-/low- level width	tкн2, tкL2	$4.0~\text{V} \le \text{EV}_\text{DD0} \le 5.5~\text{V}$		tксү2/2 – 7		tксу2/2 -7		tксү2/2 - 7		ns
		$2.7~\text{V} \leq \text{EV}_{\text{DDO}} \leq 5.5~\text{V}$		tксү2/2 – 8		tксу2/2 - 8		tксу2/2 - 8		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		tксу2/2 — 18		tксу2/2 - 18		tксу2/2 - 18		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		tксү2/2 – 66		tксу2/2 - 66		tксү2/2 - 66		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5	$1.6~V \leq EV_{DD0} \leq 5.5~V$			tксу2/2 - 66		tксу2/2 - 66		ns

(Notes, Caution, and Remarks are listed on the next page.)

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)

(Ta = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	HS (high	•	`	/-speed Mode	LV (low main)	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$\begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned}$	1/f _{MCK} + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$\label{eq:section_section} \begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1/f _{MCK} + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	1/f _{MCK} + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$\label{eq:section} \begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1/f _{MCK} + 190 Note 3		1/fMCK + 190 Note 3		1/fmck + 190 Note 3		kHz
		$ \begin{aligned} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{aligned} $	1/f _{MCK} + 190 Note 3		1/fMCK + 190 Note 3		1/fmck + 190 Note 3		kHz
Data hold time (transmission)	thd:dat	$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	0	305	0	305	0	305	ns
		$ \begin{aligned} &2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	0	305	0	305	0	305	ns
		$ \begin{cases} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{cases} $	0	355	0	355	0	355	ns
		eq:second-seco	0	355	0	355	0	355	ns
		$\begin{split} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	0	405	0	405	0	405	ns

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

- 2. Use it with $EV_{DD0} \ge V_b$.
- 3. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI16 to ANI26

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condit	ions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL 10-bit resolution		$1.8~V \leq AV_{REFP} \leq 5.5~V$		1.2	±5.0	LSB
		EVDD0 = AV _{REFP} = V _{DD} Notes 3, 4	$\begin{array}{ c c c }\hline 1.6 \ V \leq AV_{REFP} \leq 5.5 \ V^{Note} \\ & & \\ &$		1.2	±8.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target ANI pin : ANI16 to	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
		ANI26	$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μS
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μS
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$			±0.35	%FSR
		EVDD0 = AVREFP = VDD Notes 3, 4	$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±0.60	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution	$1.8~V \le AV_{REFP} \le 5.5~V$			±0.35	%FSR
		EVDD0 = AVREFP = VDD Notes 3, 4	$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±0.60	%FSR
Integral linearity error ^{Note}	ILE	10-bit resolution	$1.8~V \le AV_{REFP} \le 5.5~V$			±3.5	LSB
1		EVDD0 = AVREFP = VDD Notes 3, 4	$1.6~V \le AV_{REFP} \le 5.5~V^{Note}$			±6.0	LSB
Differential linearity	DLE	10-bit resolution	$1.8~V \le AV_{REFP} \le 5.5~V$			±2.0	LSB
error ^{Note 1}		EVDD0 = AVREFP = VDD Notes 3, 4	$1.6~V \le AV_{REFP} \le 5.5~V^{Note}$			±2.5	LSB
Analog input voltage	VAIN	ANI16 to ANI26	,	0		AVREFP and EVDD0	٧

- **Notes 1.** Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

- **4.** When $AV_{REFP} < EV_{DD0} \le V_{DD}$, the MAX. values are as follows.
 - Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.

5. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (Ta = -40 to $+105^{\circ}$ C, 2.4 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V, Vss = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2}	HALT	HS (high-	fih = 32 MHz Note 4	V _{DD} = 5.0 V		0.62	3.40	mA
Current Note 1	Note 2	mode	speed main) mode Note 7		V _{DD} = 3.0 V		0.62	3.40	mA
			mode	fin = 24 MHz Note 4	V _{DD} = 5.0 V		0.50	2.70	mA
					V _{DD} = 3.0 V		0.50	2.70	mA
				fin = 16 MHz Note 4	V _{DD} = 5.0 V		0.44	1.90	mA
					V _{DD} = 3.0 V		0.44	1.90	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.31	2.10	mA
		speed main) mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.48	2.20	mA	
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.31	2.10	mA
			V _{DD} = 3.0 V	Resonator connection		0.48	2.20	mA	
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.21	1.10	mA
				V _{DD} = 5.0 V	Resonator connection		0.28	1.20	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.21	1.10	mA
				V _{DD} = 3.0 V	Resonator connection		0.28	1.20	mA
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.28	0.61	μΑ
			clock operation	T _A = -40°C	Resonator connection		0.47	0.80	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.34	0.61	μΑ
				T _A = +25°C	Resonator connection		0.53	0.80	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.41	2.30	μΑ
				T _A = +50°C	Resonator connection		0.60	2.49	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.64	4.03	μΑ
				T _A = +70°C	Resonator connection		0.83	4.22	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		1.09	8.04	μΑ
				T _A = +85°C	Resonator connection		1.28	8.23	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		5.50	41.00	μΑ
				T _A = +105°C	Resonator connection		5.50	41.00	μΑ
	IDD3 ^{Note 6}	STOP	T _A = -40°C				0.19	0.52	μΑ
		mode ^{Note 8}	T _A = +25°C				0.25	0.52	μΑ
			T _A = +50°C				0.32	2.21	μΑ
			T _A = +70°C				0.55	3.94	μΑ
			T _A = +85°C				1.00	7.95	μΑ
			T _A = +105°C				5.00	40.00	μΑ

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVSSO, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 32 MHz $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 16 MHz

- 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$

3.4 AC Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Items	Symbol		Conditions	3	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Tcy	Main	HS (high-speed	$1 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0.03125		1	μS
instruction execution time)		system clock (fmain) operation	main) mode	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μS
		Subsystem of operation	clock (fsua)	$2.4~V \le V_{DD} \le 5.5~V$	28.5	30.5	31.3	μS
		In the self	HS (high-speed	$1 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0.03125		1	μS
		programming mode	main) mode	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μS
External system clock frequency	fex	$2.7 \text{ V} \leq \text{V}_{DD} \leq$	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$		1.0		20.0	MHz
		2.4 V ≤ V _{DD} <	< 2.7 V		1.0		16.0	MHz
	fexs		32		35	kHz		
External system clock input high-	texh, texl	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			24			ns
evel width, low-level width		2.4 V ≤ V _{DD} <	$2.4~V \leq V_{DD} < 2.7~V$					ns
	texhs, texhs				13.7			μS
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	tтін, tтіL				1/fмск+10			ns ^{Note}
TO00 to TO07, TO10 to TO17	f то	HS (high-spe	eed 4.0 V	≤ EV _{DD0} ≤ 5.5 V			16	MHz
output frequency		main) mode	2.7 V	≤ EV _{DD0} < 4.0 V			8	MHz
			2.4 V	≤ EV _{DD0} < 2.7 V			4	MHz
PCLBUZ0, PCLBUZ1 output	fpcL	HS (high-spe	eed 4.0 V	≤ EV _{DD0} ≤ 5.5 V			16	MHz
frequency		main) mode	2.7 V	≤ EV _{DD0} < 4.0 V			8	MHz
			2.4 V	≤ EV _{DD0} < 2.7 V			4	MHz
Interrupt input high-level width,	tinth,	INTP0	2.4 V	$\leq V_{DD} \leq 5.5 \text{ V}$	1			μS
low-level width	tintl	INTP1 to INT	TP11 2.4 V	$\leq EV_{DD0} \leq 5.5 V$	1			μS
Key interrupt input low-level width	t kr	KR0 to KR7	2.4 V	$\leq EV_{DD0} \leq 5.5 \text{ V}$	250			ns
RESET low-level width	trsL		•		10			μS

Note The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$ $2.4V \le EV_{DD0} < 2.7 \text{ V}$: MIN. 125 ns

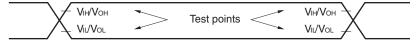
Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).

m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-spee	Unit	
				MIN.	MAX.	
Transfer rate Note 1					fmck/12 Note 2	bps
			Theoretical value of the maximum transfer rate fclk = 32 MHz, fMck = fclk		2.6	Mbps

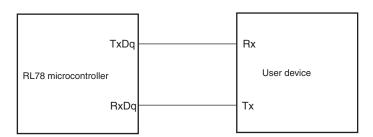
Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The following conditions are required for low voltage interface when EVDDO < VDD.

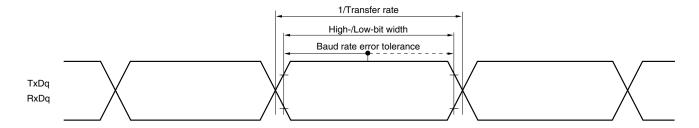
 $2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$: MAX. 1.3 Mbps

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

2. fmck: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00 to 03, 10 to 13))

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (1/2) (T_A = -40 to +105°C, 2.4 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V, Vss = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$		400 Note 1	kHz
		$\begin{aligned} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$		400 Note 1	kHz
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $		100 Note 1	kHz
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$		100 Note 1	kHz
		$\begin{aligned} &2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{aligned}$		100 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$\begin{aligned} 4.0 & \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 & \ V \leq V_b \leq 4.0 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	1200		ns
		$\begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	1200		ns
		$\begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned}$	4600		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$	4600		ns
		$2.4 \ V \leq EV_{DD0} < 3.3 \ V,$ $1.6 \ V \leq V_b \leq 2.0 \ V,$ $C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega$	4650		ns
Hold time when SCLr = "H"	tнівн	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	620		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$	500		ns
		$\begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned}$	2700		ns
		$\begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	2400		ns
		$2.4 \ V \leq EV_{DD0} < 3.3 \ V,$ $1.6 \ V \leq V_b \leq 2.0 \ V,$ $C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega$	1830		ns

(${f Notes}$ and ${f Caution}$ are listed on the next page, and ${f Remarks}$ are listed on the page after the next page.)

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{\text{BGR}}^{\text{Note 3}}, \text{Reference voltage (-)} = \text{AV}_{\text{REFM}}^{\text{Note 4}} = 0 \text{ V}, \text{HS (high-speed main) mode)}$

Parameter	Symbol	Cond	MIN.	TYP.	MAX.	Unit	
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±1.0	LSB
Analog input voltage	Vain			0		V _{BGR} Note 3	V

- **Notes 1.** Excludes quantization error ($\pm 1/2$ LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.
 - 4. When reference voltage (-) = Vss, the MAX. values are as follows.
 Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.
 Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.
 Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

3.6.2 Temperature sensor/internal reference voltage characteristics

(Ta = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, Ta = +25°C		1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs